

Diode

Fast switching Emitter Controlled 3 diode chip
SIDC08D120H8

Data Sheet

Industrial Power Control



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Fast switching Emitter Controlled 3 diode chip

Features:

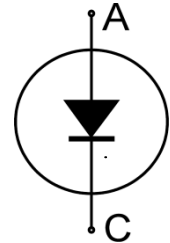
- 1200V Emitter Controlled technology
120µm chip
- Soft, fast switching
- Low reverse recovery charge
- Small temperature coefficient

Recommended for:

- Power modules
- Discrete devices

Applications:

- SMPS
- Resonant applications
- Drives



Chip Type	V_R	I_{FN}	Die Size	Package
SIDC08D120H8	1200V	10A	3.70mm x 2.20mm	Sawn on foil

Mechanical Parameters

Die size	3.70 x 2.20		mm ²
Area total	8.14		
Anode pad size	2.98 x 1.48		
Silicon thickness	120		µm
Wafer size	200		mm
Maximum possible chips per wafer	3420		
Passivation frontside	Photoimide		
Pad metal	3200nm AlSiCu		
Backside metal	Ni Ag – system To achieve a reliable solder connection it is strongly recommended not to consume the Ni layer completely during production process		
Die bond	Electrically conductive epoxy glue and soft solder		
Wire bond	Al, ≤500µm		
Reject ink dot size	Ø 0.65mm; max 1.2mm		
Storage environment (<6 months)	for original and sealed MBB bags	Ambient atmosphere air, temperature 17°C – 25°C	
	for open MBB bags	Acc. IEC 62258-3; Section 9.4 Storage Environment.	

Maximum Ratings

In general, from reliability and lifetime point of view, the lower the operation junction temperature and/or the applied voltage, the greater the expected lifetime of any semiconductor device.

Not subject to production test, specified by design.

Parameter	Symbol	Conditions	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25^{\circ}\text{C}$	1200	V
Continuous forward current, limited by $T_{vj\ max}^1$	I_F	$T_{vj} \leq 150^{\circ}\text{C}$	10	A
Maximum repetitive forward current, limited by $T_{vj\ max}$	I_{FRM}	$T_{vj} \leq 150^{\circ}\text{C}$	20	
Virtual junction temperature	T_{vj}		-40...+175	$^{\circ}\text{C}$
Virtual junction operating temperature	T_{vjop}		-40...+150	

Static Characteristics (tested on wafer), $T_{vj}=25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Reverse leakage current	I_R	$V_R = 1200\text{V}$	-	-	27.0	μA
Cathode-anode breakdown voltage	V_{BR}	$I_R = 0.25\text{mA}$	1200	-	-	V
Forward voltage drop	V_F	$I_F = 10\text{A}$	1.23	1.6	1.97	

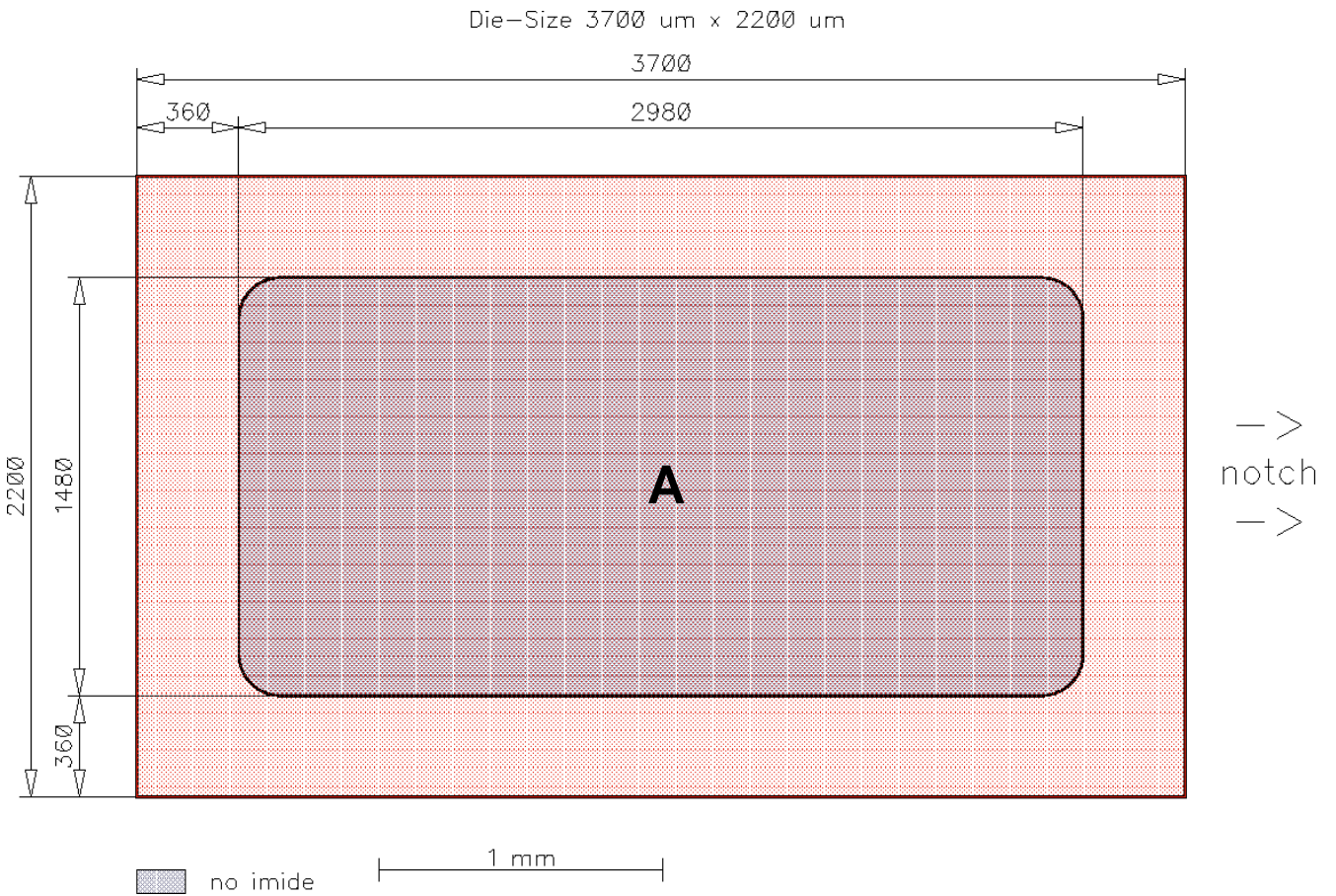
Further Electrical Characteristics

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

Application example	FS10R12VT3	Rev. 2.0
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¹ Depending on thermal properties of assembly.

Chip Drawing



A = Anode pad



SIDC08D120H8

Bare Die Product Specifics

Test coverage at wafer level cannot cover all application conditions. Therefore it is recommended to test all characteristics which are relevant for the application at package level, including RBSOA and SCSOA.

Description

AQL 0.65 for visual inspection according to failure catalogue

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Revision History

Revision	Subjects (major changes since last revision)	Date
2.0	Final data sheet	30.12.2014
2.1	Editorial changes	14.10.2015
2.2	Editorial changes (die size X/Y inverted)	25.01.2018



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